HAF2015RJ

Silicon N Channel MOS FET Series
Power Switching

REJ03G1141-0300
Rev.3.00
Aug 27, 2007

Description

This FET has the over temperature shut-down capability sensing to the junction temperature.

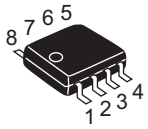
This FET has the built-in over temperature shut-down circuit in the gate area. And this circuit operation to shut-down the gate voltage in case of high junction temperature like applying over power consumption, over current etc.

Features

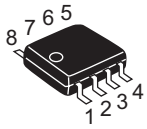
- Logic level operation (5 to 6 V Gate drive)
- High endurance capability against to the short circuit
- Built-in the over temperature shut-down circuit
- Temperature hysteresis type.
- High density mounting.

Outline

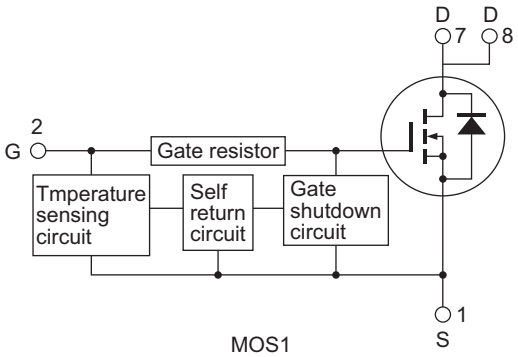
RENESAS Package code: PRSP0008DD-A
(Package name: SOP-8 <FP-8DA>)

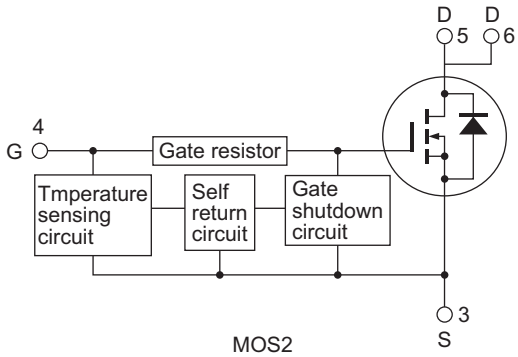


RENESAS Package code: PRSP0008DD-D
(Package name: SOP-8 <FP-8DAV>)



1, 3	Source
2, 4	Gate
5, 6, 7, 8	Drain





Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	V_{DSS}	60	V
Gate to source voltage	V_{GSS}	16	V
	V_{GSS}	–2.5	V
Drain current	I_D	2	A
Drain peak current	$I_{D\ (pulse)}$ Note 1	4	A
Body-drain diode reverse drain current	I_{DR}	2	A
Avalanche current	I_{AP} Note 4	0.54	A
Avalanche energy	E_{AR} Note 4	25	mJ
Channel dissipation	Pch Note 2	2	W
Channel dissipation	Pch Note 3	1.5	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	–55 to +150	°C

Notes: 1. PW ≤ 10 µs, duty cycle ≤ 1%
2. 1 Drive operation: When using the glass epoxy board (FR4 40 × 40 × 1.6 mm), PW ≤ 10 s
3. 2 Drive operation: When using the glass epoxy board (FR4 40 × 40 × 1.6 mm), PW ≤ 10 s
4. Tch = 25°C, Rg > 50 Ω

Typical Operation Characteristics

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Input voltage	V_{IH}	3.5	—	—	V	
	V_{IL}	—	—	1.2	V	
Input current (Gate non shut down)	I_{IH1}	—	—	100	µA	Vi = 5 V, V_{DS} = 0
	I_{IH2}	—	—	50	µA	Vi = 3.5 V, V_{DS} = 0
	I_{IL}	—	—	1	µA	Vi = 1.2 V, V_{DS} = 0
Input current (Gate shut down)	$I_{IH\ (sd)\ 1}$	—	0.53	—	mA	Vi = 8 V, V_{DS} = 0
	$I_{IH\ (sd)\ 2}$	—	0.2	—	mA	Vi = 3.5 V, V_{DS} = 0
Shut down temperature	Tsd	—	175	—	°C	Channel temperature
Hysteresis temperature	Thr	—	120	—	°C	Channel temperature
Gate operation voltage	V_{OP}	3.5	—	12	V	

Electrical Characteristics

(Ta = 25°C)

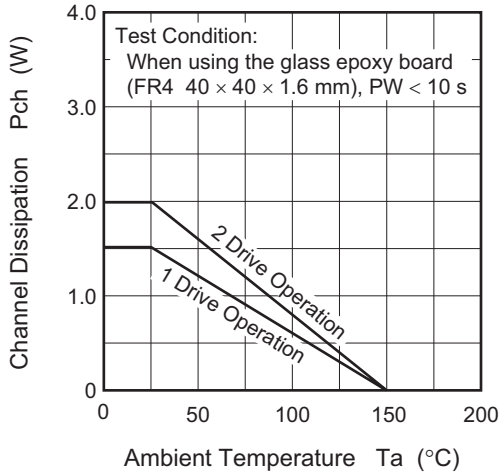
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain current	I_{D1}	0.7	—	—	A	V_{GS} = 3.5 V, V_{DS} = 2 V
	I_{D2}	—	—	10	mA	V_{GS} = 1.2 V, V_{DS} = 2 V
Drain to source breakdown voltage	$V_{(BR)\ DSS}$	60	—	—	V	I_D = 10 mA, V_{GS} = 0
Gate to source breakdown voltage	$V_{(BR)\ GSS}$	16	—	—	V	I_G = 500 µA, V_{DS} = 0
	$V_{(BR)\ GSS}$	–2.5	—	—	V	I_G = –100 µA, V_{DS} = 0
Gate to source leak current	I_{GSS1}	—	—	100	µA	V_{GS} = 5 V, V_{DS} = 0
	I_{GSS2}	—	—	50	µA	V_{GS} = 3.5 V, V_{DS} = 0
	I_{GSS3}	—	—	1	µA	V_{GS} = 1.2 V, V_{DS} = 0
	I_{GSS4}	—	—	–100	µA	V_{GS} = –2.4 V, V_{DS} = 0
Input current (shut down)	$I_{GS\ (op)\ 1}$	—	0.53	—	mA	V_{GS} = 8 V, V_{DS} = 0
	$I_{GS\ (op)\ 2}$	—	0.2	—	mA	V_{GS} = 3.5 V, V_{DS} = 0
Zero gate voltage drain current	I_{DSS1}	—	—	10	µA	V_{DS} = 60 V, V_{GS} = 0
	I_{DSS2}	—	—	10	µA	V_{DS} = 48 V, V_{GS} = 0 Ta = 125°C
Gate to source cutoff voltage	$V_{GS\ (off)}$	1.4	—	2.5	V	I_D = 1 mA, V_{DS} = 10 V
Static drain to source on state resistance	$R_{DS\ (on)}$	—	130	200	mΩ	I_D = 1 A, V_{GS} = 5 V Note 5
	$R_{DS\ (on)}$	—	110	160	mΩ	I_D = 1 A, V_{GS} = 10 V Note 5
Forward transfer admittance	$\|y_{fs}\|$	0.5	2.5	—	S	I_D = 1 A, V_{DS} = 10 V Note 5
Output capacitance	Coss	—	139	—	pF	V_{DS} = 10 V, V_{GS} = 0 f = 1 MHz
Turn-on delay time	$t_{d\ (on)}$	—	4.2	—	µs	I_D = 1 A V_{GS} = 5 V R_L = 30 Ω
Rise time	t_r	—	20	—	µs	
Turn-off delay time	$t_{d\ (off)}$	—	1	—	µs	
Fall time	t_f	—	1	—	µs	
Body-drain diode forward voltage	V_{DF}	—	0.82	—	V	I_F = 2 A, V_{GS} = 0
Body-drain diode reverse recovery time	t_{rr}	—	55	—	ns	I_F = 2 A, V_{GS} = 0 di_F/dt = 50 A/µs
Over load shut down operation time Note6	t_{os1}	—	15	—	ms	V_{GS} = 5 V, V_{DD} = 16 V

Notes: 5. Pulse test

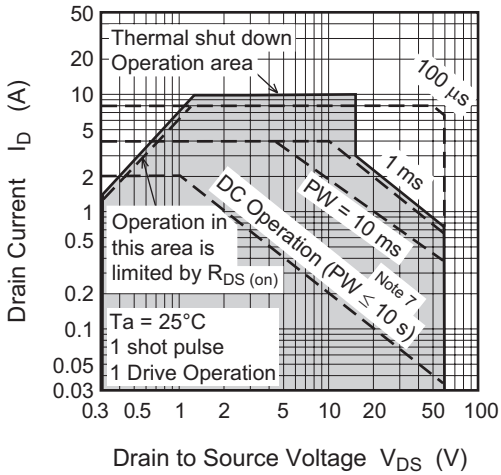
6. Including the junction temperature rise of the over loaded condition.

Main Characteristics

Power vs. Temperature Derating

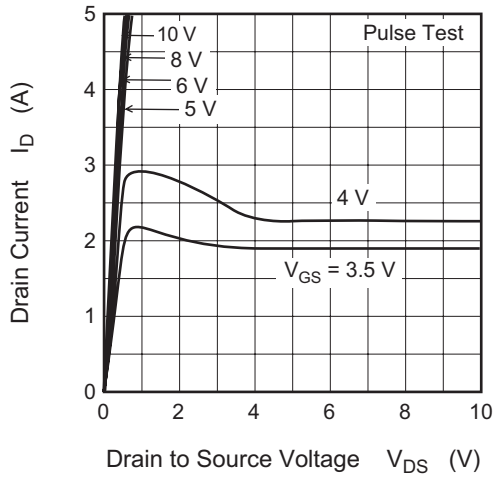


Maximum Safe Operation Area

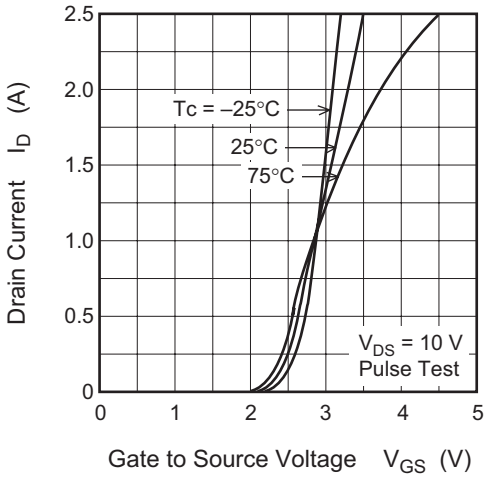


Note 7:
When using the glass epoxy board
(FR4 40 × 40 × 1.6 mm)

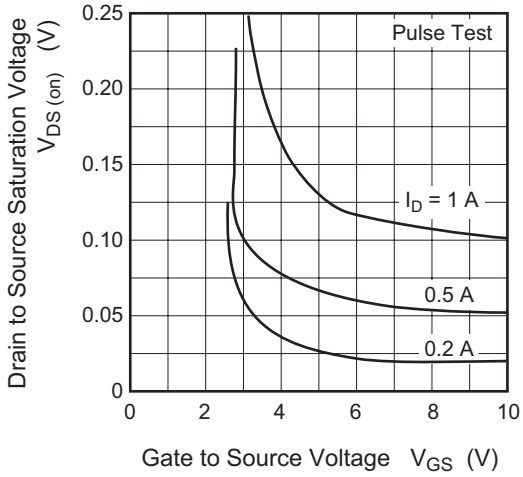
Typical Output Characteristics



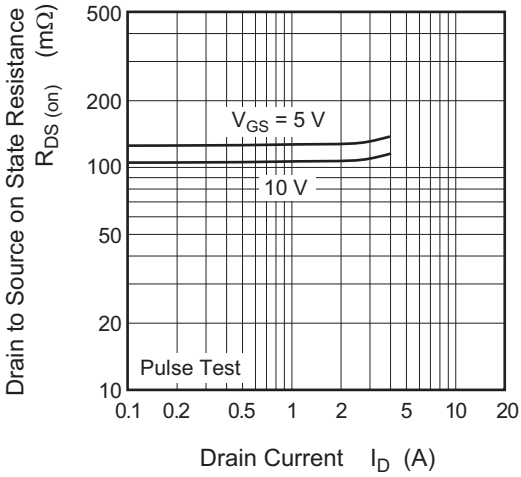
Typical Transfer Characteristics



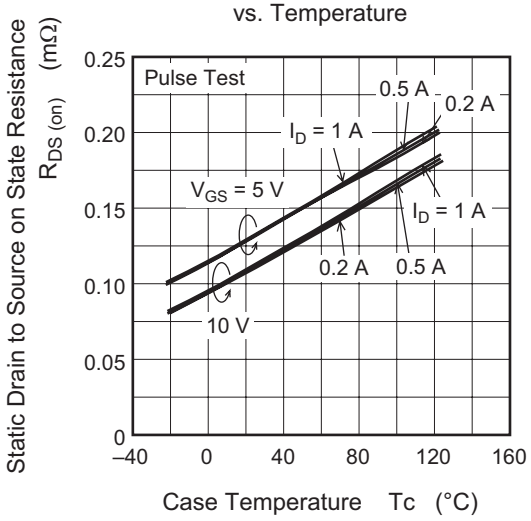
Drain to Source Saturation Voltage vs.
Gate to Source Voltage



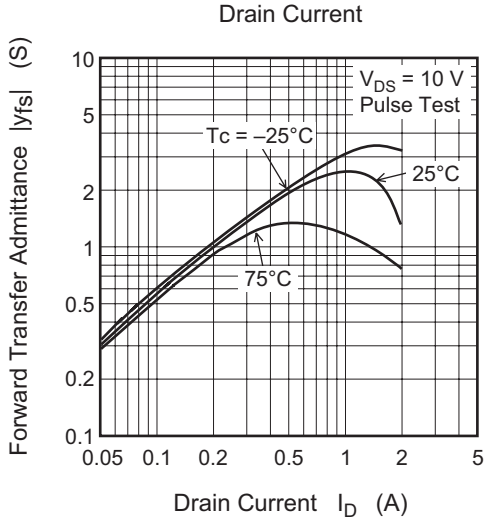
Static Drain to Source on State Resistance
vs. Drain Current



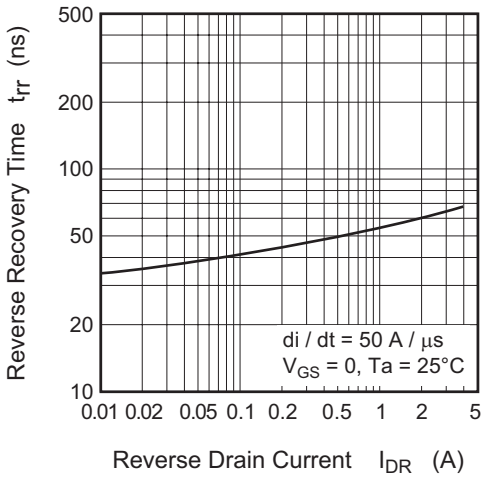
Static Drain to Source on State Resistance vs. Temperature



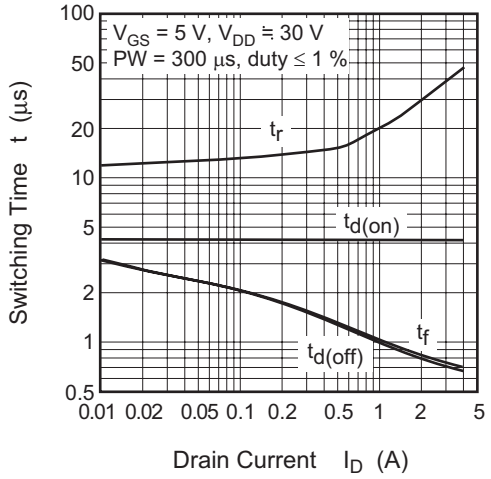
Forward Transfer Admittance vs. Drain Current



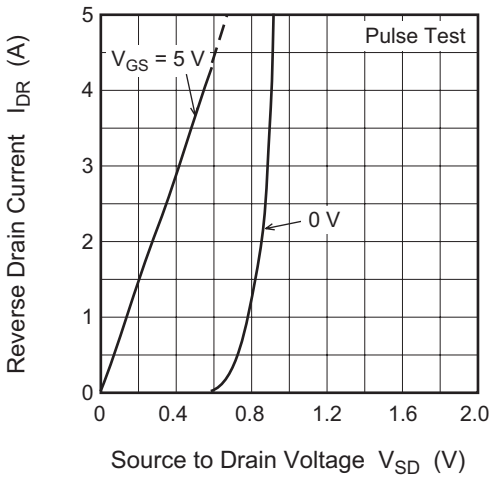
Body-Drain Diode Reverse Recovery Time



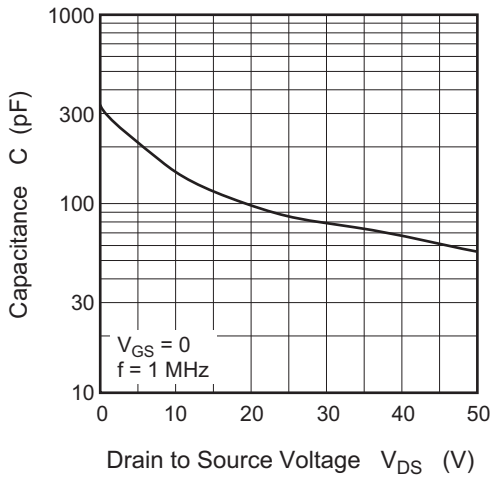
Switching Characteristics



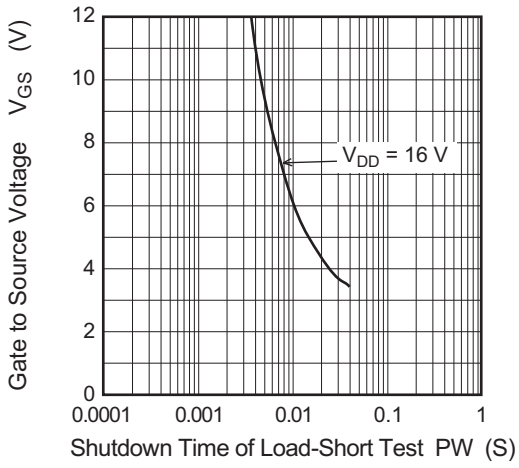
Reverse Drain Current vs. Source to Drain Voltage



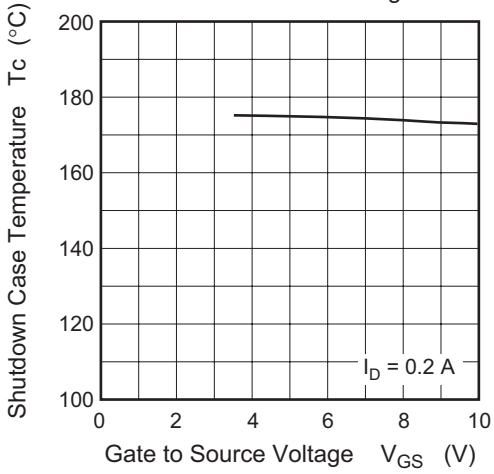
Typical Capacitance vs. Drain to Source Voltage



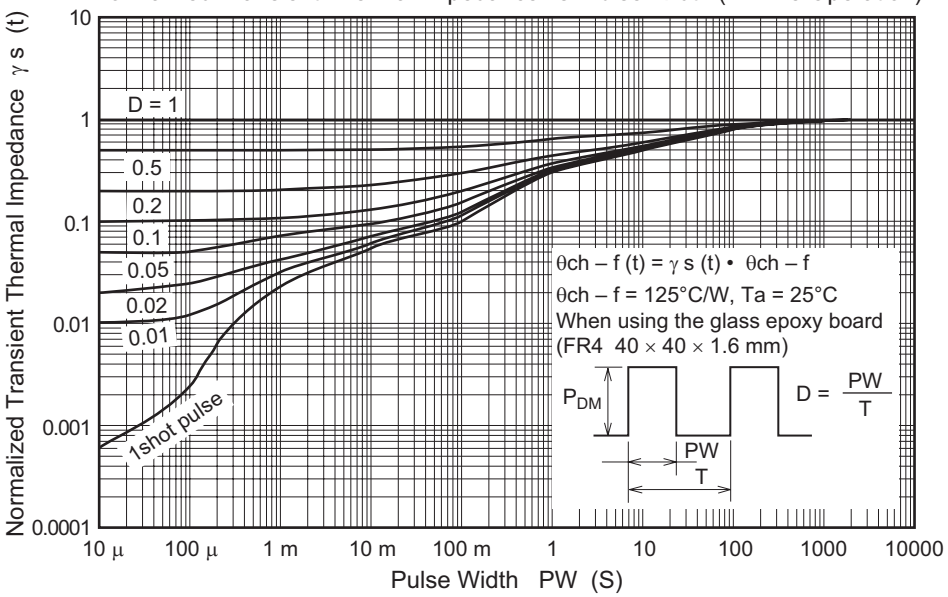
Gate to Source Voltage vs.
Shutdown Time of Load-Short Test



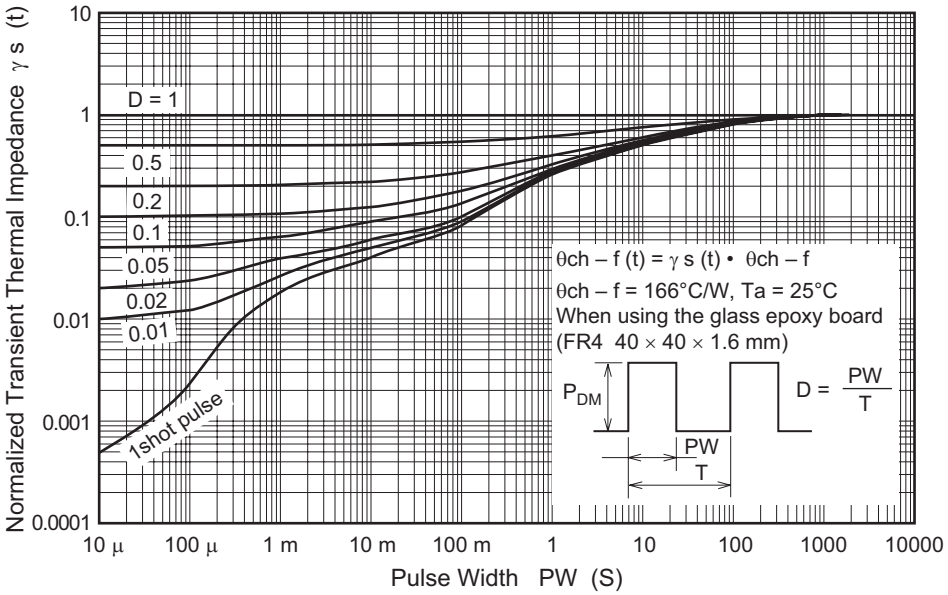
Shutdown Case Temperature vs.
Gate to Source Voltage



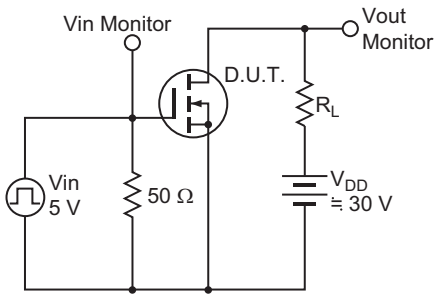
Normalized Transient Thermal Impedance vs. Pulse Width (1 Drive Operation)



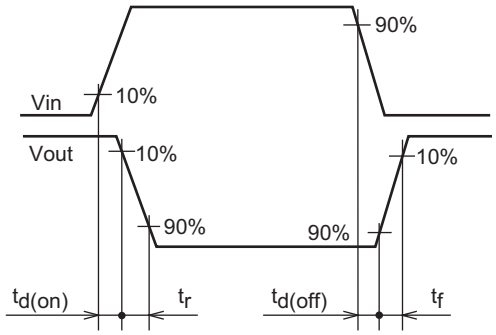
Normalized Transient Thermal Impedance vs. Pulse Width (2 Drive Operation)



Switching Time Test Circuit

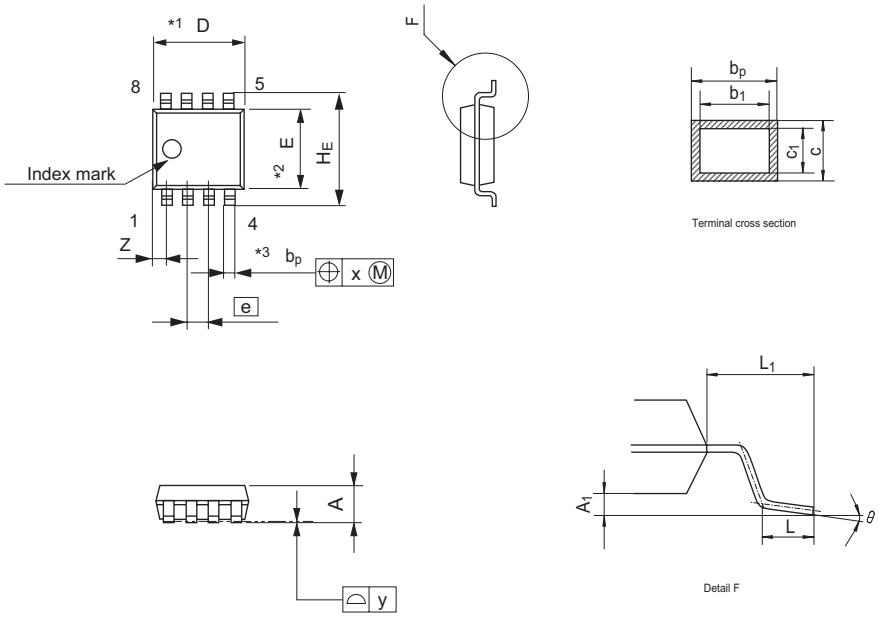


Waveform



Package Dimensions

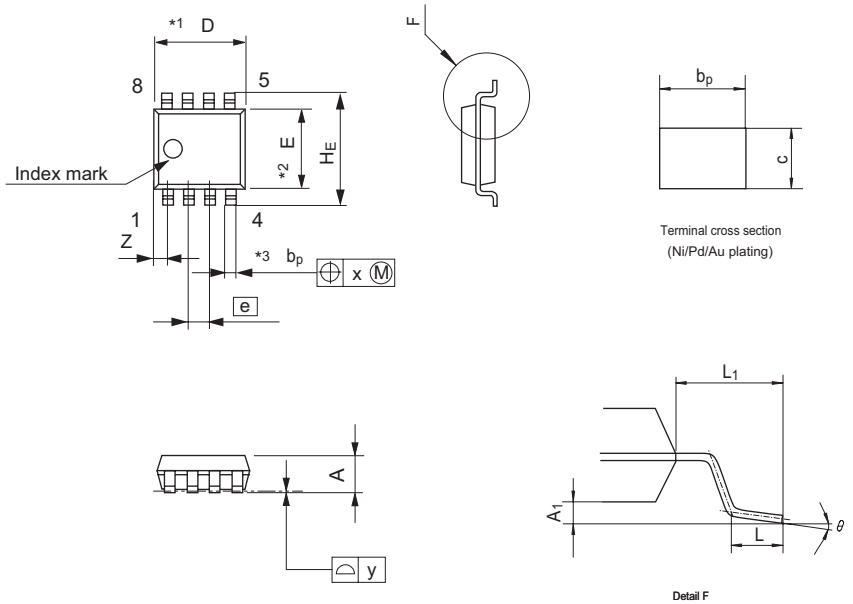
Package Name	JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
SOP-8	P-SOP8-3.95 × 4.9-1.27	PRSP0008DD-A	FP-8DA	0.085g



NOTE)
1. DIMENSIONS "*1(Nom)" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	—	4.90	5.3
E	—	3.95	—
A_2	—	—	—
A_1	0.10	0.14	0.25
A	—	—	1.75
b_p	0.34	0.42	0.50
b_1	—	0.40	—
c	0.19	0.22	0.25
c_1	—	0.20	—
θ	0°	—	8°
H_E	5.80	6.10	6.20
e	—	1.27	—
x	—	—	0.25
y	—	—	0.1
Z	—	—	0.75
L	0.40	0.60	1.27
L_1	—	1.08	—

Package Name	JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
SOP-8	P-SOP8-3.95 × 4.9-1.27	PRSP0008DD-D	FP-8DAV	0.085g



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Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	—	4.90	5.3
E	—	3.95	—
A_2	—	—	—
A_1	0.10	0.14	0.25
A	—	—	1.75
b_p	0.34	0.40	0.46
b_1	—	—	—
c	0.15	0.20	0.25
c_1	—	—	—
θ	0°	—	8°
H_E	5.80	6.10	6.20
e	—	1.27	—
x	—	—	0.25
y	—	—	0.1
Z	—	—	0.75
L	0.40	0.60	1.27
L_1	—	1.08	—

Ordering Information

Part No.	Quantity	Shipping Container
HAF2015RJ-EL	2500 pcs/Reel	Embossed tape

Renesas Technology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

RENESAS SALES OFFICES

http://www.renesas.com

Refer to "**http://www.renesas.com/en/network**" for the latest and detailed information.

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Colophon .7.0